**Product data sheet** 

## 1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

## 2. Features and benefits

- · High blocking voltage capability
- High noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

## 3. Applications

- General purpose motor control
- · General purpose switching

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute	maximum rating					
$V_{DRM}$	repetitive peak off-state voltage		600			V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 91 °C; Fig. 1; Fig. 2; Fig. 3	25			А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; $t_p = 20 \text{ms}$ ; Fig. 4; Fig. 5	190		А	
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	6	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2+ G-;}$ $T_j = 25 \text{ °C; Fig. 7}$	-	10	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	11	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	23	70	mA

4Q Triad

# 5. Pinning information

**Table 2. Pinning information** 

Graphic symbol
T2T1
sym051
symus i

## 6. Ordering information

### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
BTA140-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

## 7. Marking

### **Table 4. Marking codes**

Type number	Marking codes
BT140-600	BT140-600

**4Q Triac** 

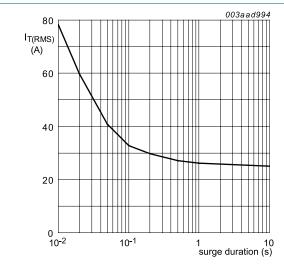
# 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 91°C; Fig 1; Fig 2; Fig 3	25	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25  ^{\circ}\text{C}$ ; $t_p = 20  \text{ms}$ ; Fig 4; Fig 5	190	А
		full sine wave; $T_{j(init)} = 25  ^{\circ}\text{C}$ ; $t_p = 16.7  \text{ms}$	209	А
l²t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	180	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 70 mA; T2+ G+	50	A/µs
		I <sub>G</sub> = 70 mA; T2+ G-	50	A/µs
		I <sub>G</sub> = 70 mA; T2- G-	50	A/µs
		I <sub>G</sub> = 140 mA; T2- G+	10	A/µs
I <sub>GM</sub>	peak gate current		2	Α
$P_{\text{GM}}$	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		125	°C

**4Q Triac** 

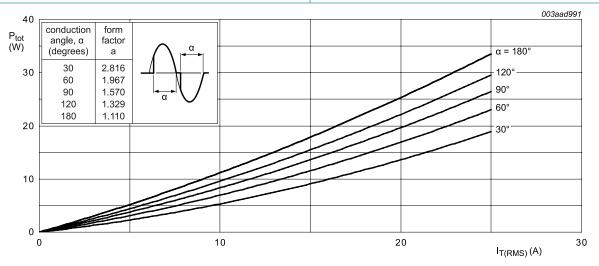


f = 50 Hz;  $T_{mb}$  = 91 °C

30 003aad995
I<sub>T(RMS)</sub>
(A)
20
10
0-50 0 50 100 T<sub>mb</sub>(°C)

Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

Fig. 1. RMS on-state current as a function of surge duration; maximum values



 $\alpha$  = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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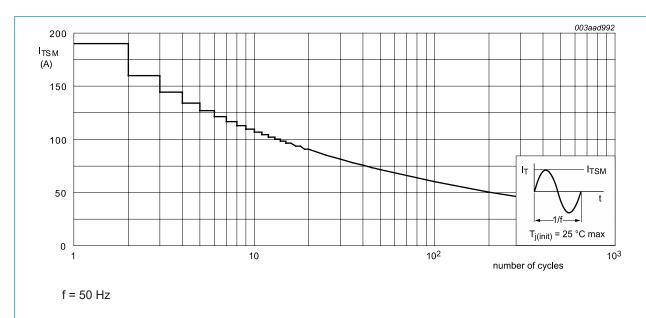
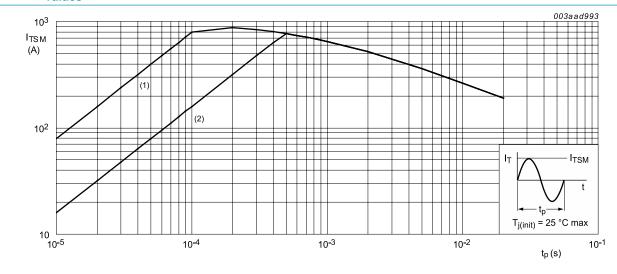


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



t<sub>p</sub> ≤ 20 ms

- (1) dl<sub>⊤</sub>/dt limit
- (2) T2- G+ quadrant limit

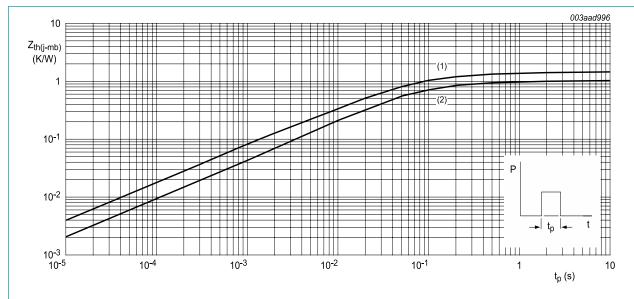
Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

**4Q Triac** 

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	full cycle; Fig 6	-	-	1	K/W
	from junction to mounting base	half cycle; <u>Fig 6</u>	-	-	1.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



- (1) Unidirectional (half cycle)
- (2) Bidirectional (full cycle)

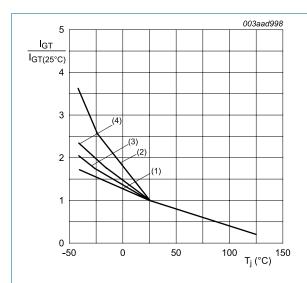
Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

**4Q Triac** 

## 10. Characteristics

## **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	gate trigger current $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; $ $T_j = 25 \text{ °C}; Fig. 7$				
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	10	35	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	11	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	23	70	mA
I <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	8	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	30	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	18	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	15	60	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; T2+; <u>Fig. 9</u>	-	7	60	mA
		V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; T2-; <u>Fig. 9</u>		12	60	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.55	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics			•		
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 402 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit		300	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 \text{ °C}; dI_{com}/dt = 9 \text{ A/}$ ms; $I_T = 25 \text{ A}; gate open circuit}$	-	10	-	V/µs
<b>t</b> <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 30 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	μs



- (1) T2+ G+
- (2) T2+ G-
- (3) T2- G-
- (4) T2- G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

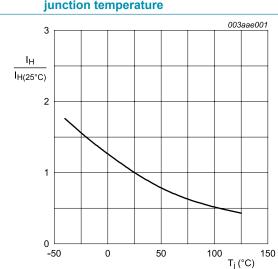


Fig. 9. Normalized holding current as a function of junction temperature

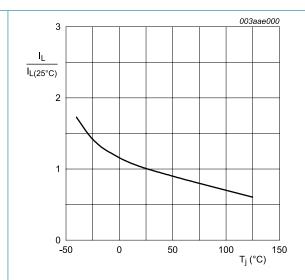
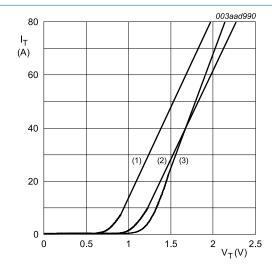


Fig. 8. Normalized latching current as a function of junction temperature



 $V_o$  = 1.073 V;  $R_s$  = 0.015  $\Omega$ 

(1)  $T_j = 125$  °C; typical values (2)  $T_j = 125$  °C; maximum values (3)  $T_j = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

**4Q Triac** 

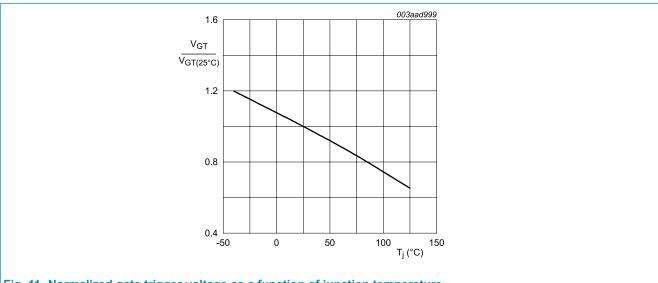
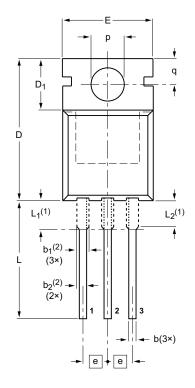


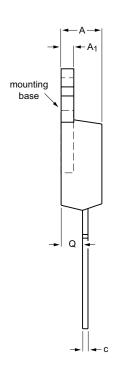
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

# 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

**SOT78** 





### **DIMENSIONS (mm are the original dimensions)**

UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

	OUTLINE		REFER	EUROPEAN	ISSUE DATE		
	VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

4Q Triad

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- Please consult the most recently issued document before initiating or completing a design.
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